ESD Protection Diode Array, 5-Line

This 5-line surge protection array is designed for application requiring transient voltage protection capability. It is intended for use in over-transient voltage and ESD sensitive equipment such as computers, printers, automotive electronics, networking communication and other applications. This device features a monolithic common anode design which protects five independent lines in a single TSOP-6 package.

Features

- Protects up to 5 Lines in a Single TSOP-6 Package
- Peak Power Dissipation 350 W (8 × 20 µs Waveform)
- ESD Rating of Class 3B (Exceeding 8.0 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model
- Compliance with IEC 61000-4-2 (ESD) 15 kV (Air), 8.0 kV (Contact)
- Flammability Rating of UL 94 V-0
- These are Pb-Free Devices

Applications

- Hand-Held Portable Applications
- Networking and Telecom
- Automotive Electronics
- Serial and Parallel Ports
- Notebooks, Desktops, Servers

MAXIMUM RATINGS (T, I = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit
P _{PK} 1	Peak Power Dissipation 8 \times 20 μs Double Exponential Waveform (Note 1)	350	W
T_J	Operating Junction Temperature Range	-40 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TL	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Air (ESD) IEC 61000-4-2 Contact (ESD)	>8000 >400 >15000 >8000	٧

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

1. Non-repetitive current pulse per Figure 3.



ON Semiconductor®

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TSOP-6 FIVE SURGE **PROTECTION** 350 W PEAK POWER

PIN ASSIGNMENT



TSOP-6 **CASE 318G** SCALE 2:1



- PIN 1. CATHODE
 - 2. ANODE
 - 3. CATHODE
 - 4. CATHODE
 - 5. CATHODE
 - 6. CATHODE

MARKING DIAGRAM



- x = SMS05C:J
 - = SMS12C:K
 - = SMS15C:L
- = SMS24C:M
- = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]		
SMS05CT1G				
SMS12CT1G	TSOP-6	3000/Tape & Reel		
SMS15CT1G	(Pb-Free)	oooo, rape a ricer		
SMS24CT1G				

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

SMS05C ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	(Note 2)			5.0	V
Breakdown Voltage	V_{BR}	I _T = 1.0 mA (Note 3)	6.2		7.2	V
Reverse Leakage Current	I _R	V _{RWM} = 5.0 V			5.0	μΑ
Clamping Voltage		I _{PP} = 5.0 A (8 × 20 μs Waveform)			9.8	V
Clamping Voltage	V _C	I _{PP} = 24 A (8 × 20 μs Waveform)			14.5	V
Maximum Peak Pulse Current	I _{PP}	8 × 20 μs Waveform			24	Α
Capacitance	CJ	V _R = 0 V, f = 1.0 MHz (Line to GND)		260	400	pF

SMS12C ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage V _{RWM}		(Note 2)			12	V
Breakdown Voltage	V_{BR}	I _T = 1.0 mA (Note 3)	13.3		15	V
Reverse Leakage Current	I _R	V _{RWM} = 12 V		0.001	1.0	μΑ
Clamping Voltage V		I_{PP} = 5.0 A (8 \times 20 μ s Waveform)			19	V
Clamping Voltage	V _C	I _{PP} = 15 A (8 × 20 μs Waveform)			23	V
Maximum Peak Pulse Current I _F		8 × 20 μs Waveform			15	Α
Capacitance		V _R = 0 V, f = 1.0 MHz (Line to GND)		120	150	pF

SMS15C ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$, unless otherwise specified) (See Note 4)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage V _{RWM}		(Note 2)			15	V
Breakdown Voltage	V_{BR}	I _T = 1.0 mA (Note 3)	17		19	V
Reverse Leakage Current	I _R	V _{RWM} = 15 V		0.05	1.0	μΑ
Clamping Voltage	V _C	I_{PP} = 5.0 A (8 $ imes$ 20 μ s Waveform)			24	V
Clamping Voltage	V _C	I _{PP} = 12 A (8 × 20 μs Waveform)			29	V
Maximum Peak Pulse Current	I _{PP}	8 × 20 μs Waveform			12	Α
Capacitance	CJ	V _R = 0 V, f = 1.0 MHz (Line to GND)		95	125	pF

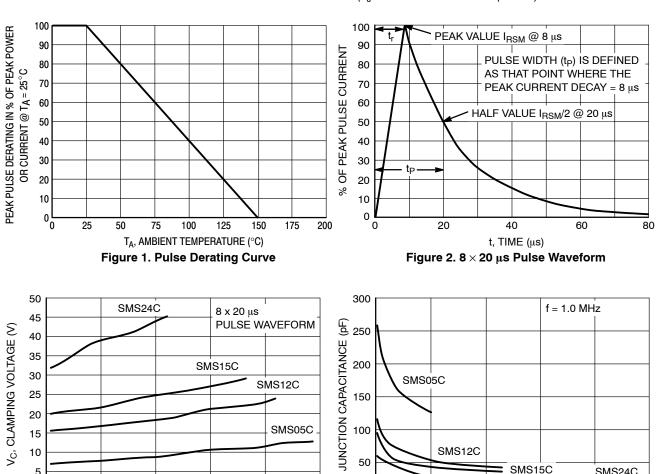
SMS24C ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	(Note 2)			24	V
Breakdown Voltage	V_{BR}	I _T = 1.0 mA (Note 3)	26.7		32	V
Reverse Leakage Current	I _R	V _{RWM} = 24 V		0.001	1.0	μΑ
Clamping Voltage	V _C	I_{PP} = 5.0 A (8 \times 20 μ s Waveform)			40	V
Clamping Voltage	V _C	I _{PP} = 8 A (8 × 20 μs Waveform)			44	V
Maximum Peak Pulse Current	I _{PP}	8 × 20 μs Waveform			8.0	Α
Capacitance	CJ	V _R = 0 V, f = 1.0 MHz (Line to GND)		60	75	pF

^{2.} Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.

^{3.} V_{BR} is measured at pulse test current I_T.
4. Parametrics are the same for the Pb–Free packages, which are suffixed with a "G".

TYPICAL PERFORMANCE CURVES (T_{.J} = 25°C unless otherwise specified)



SMS05C

25

20

IPP, PEAK PULSE CURRENT (A) Figure 3. Clamping Voltage vs. Peak Pulse Current

15

10

15

10

5

0

Figure 4. Junction Capacitance vs. Reverse Voltage

V_{BR}, REVERSE VOLTAGE (V)

10

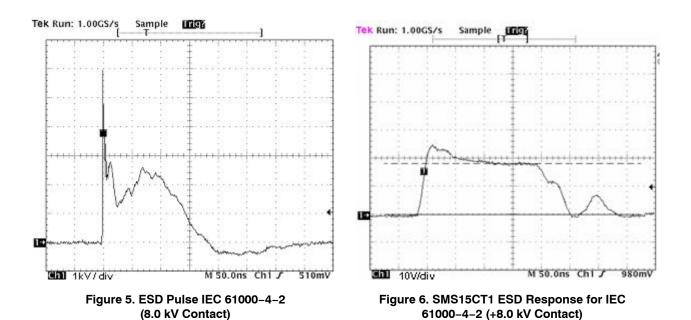
SMS15C

SMS24C

25

20

SMS12C



0

TYPICAL COMMON ANODE APPLICATIONS

A 5 surge protection junction common anode design in a TSOP-6 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design

especially when board space is at a premium. A simplified example of SMS05C Series Device applications is illustrated below.

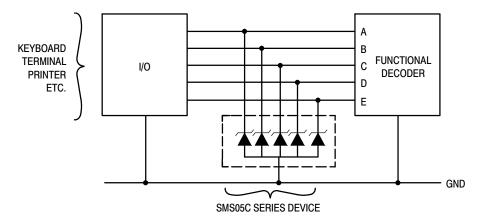


Figure 7. Computer Interface Protection

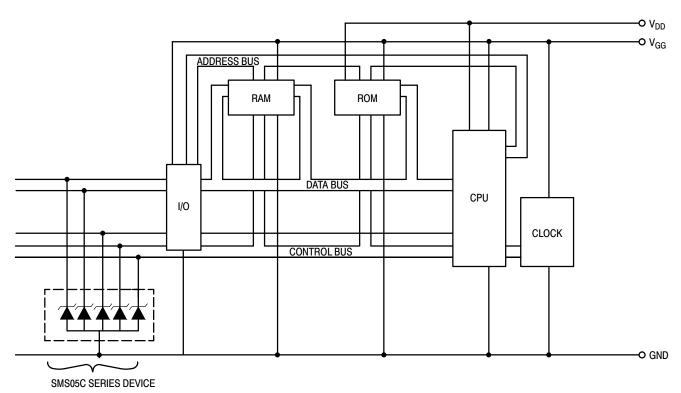
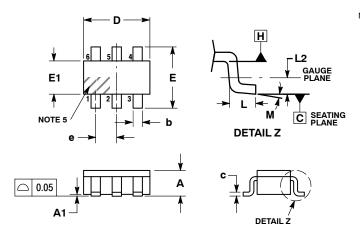


Figure 8. Microprocessor Protection

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE V

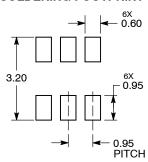


NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
- LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
- PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	0.90	1.00	1.10			
A1	0.01	0.06	0.10			
b	0.25	0.38	0.50			
С	0.10	0.18	0.26			
D	2.90	3.00	3.10			
E	2.50	2.75	3.00			
E1	1.30	1.50	1.70			
е	0.85	0.95	1.05			
L	0.20	0.40	0.60			
L2	0.25 BSC					
М	0° – 10°					

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS *For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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